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Team Nexperia

# 74AHC139; 74AHCT139

### **Dual 2-to-4 line decoder/demultiplexer**

Rev. 02 — 9 May 2008

**Product data sheet** 

#### 1. General description

The 74AHC139; 74AHCT139 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC139; 74AHCT139 is a high-speed, dual 2-to-4 line decoder/demultiplexer. This device has two independent decoders, each accepting two binary weighted inputs (nA0 and nA1) and providing four mutually exclusive active LOW outputs ( $n\overline{Y}0$  to  $n\overline{Y}3$ ). Each decoder has an active LOW enable input ( $n\overline{E}$ ). When  $n\overline{E}$  is HIGH, every output is forced HIGH. The enable input can be used as the data input for a 1-to-4 demultiplexer application.

The 74AHC139; 74AHCT139 is identical to the HEF4556 of the HE4000B family.

#### 2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V<sub>CC</sub>
- Input levels:
  - ◆ For 74AHC139: CMOS level
  - ◆ For 74AHCT139: TTL level
- ESD protection:
  - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
  - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

### 3. Ordering information

Table 1. Ordering information

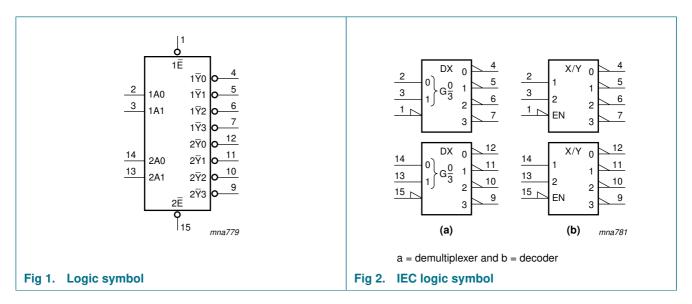
Type number	Package											
	Temperature range	Name	Description	Version								
74AHC139												
74AHC139D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1								
74AHC139PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1								

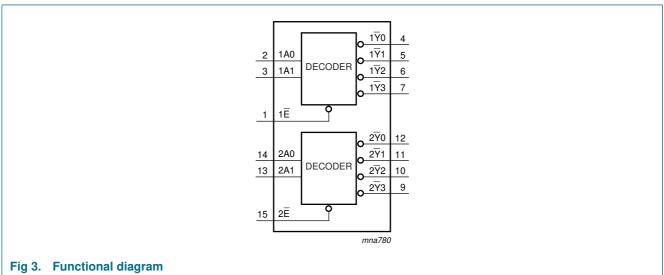


 Table 1.
 Ordering information ...continued

Type number	Package										
	Temperature range	Name	Description	Version							
74AHCT139		'									
74AHCT139D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1							
74AHCT139PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1							

### 4. Functional diagram

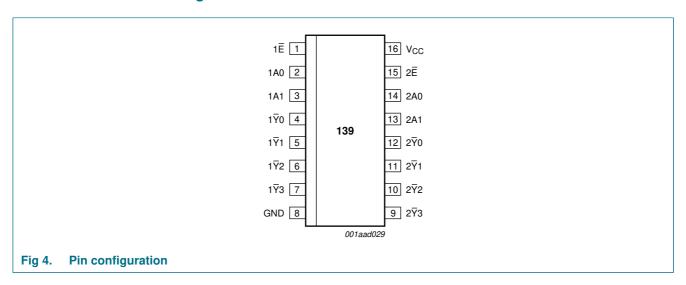




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### 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Ē	1	enable input (active LOW)
1A0	2	address input
1A1	3	address input
1 <u></u> 70	4	output
1 <u></u> 71	5	output
1 <del>\</del> Y2	6	output
1 <del>\</del> 73	7	output
GND	8	ground (0 V)
2 <del>\overline{Y}</del> 3	9	output
2 <del>¥</del> 2	10	output
2 <u>₹</u> 1	11	output
$2\overline{Y}0$	12	output
2A1	13	address input
2A0	14	address input
2Ē	15	enable input (active LOW)
$V_{CC}$	16	supply voltage

### 6. Functional description

Table 3. Function table[1]

Control	Input		Output	Output								
nĒ	nA0	nA1	n <del></del> ₹0	n <del></del> ₹1	n₹2	n <del></del> ₹3						
Н	Χ	X	Н	Н	Н	Н						
L	L	L	L	Н	Н	Н						
	Н	L	Н	L	Н	Н						
	L	Н	Н	Н	L	Н						
	Н	Н	Н	Н	Н	L						

<sup>[1]</sup> H = HIGH voltage level;

### 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_1 < -0.5 \text{ V}$	<u>[1]</u> –20	-	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> –20	+20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I <sub>CC</sub>	supply current		-	+75	mA
I <sub>GND</sub>	ground current		<b>-75</b>	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C}$ to $+125  ^{\circ}\text{C}$	[2] _	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

L = LOW voltage level;

X = don't care.

<sup>[2]</sup> For SO16 packages: above 70 °C the value of  $P_{tot}$  derates linearly at 8 mW/K. For TSSOP16 packages: above 60 °C the value of  $P_{tot}$  derates linearly at 5.5 mW/K.

### 8. Recommended operating conditions

Table 5. Operating conditions

	oporating conditions					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC1	39					
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V
74AHCT	139					
V <sub>CC</sub>	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

### 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74AHC13	39		•			'				
$V_{IH}$	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	-	-	1.5	-	1.5	-	٧
	input voltage	$V_{CC} = 3.0 \text{ V}$	2.1	-	-	2.1	-	2.1	-	٧
		$V_{CC} = 5.5 \text{ V}$	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 3.0 \text{ V}$	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	٧
		$I_{O} = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	٧
		$I_O = -50 \mu A$ ; $V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	٧
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	,	–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μΑ
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
C <sub>O</sub>	output capacitance		-	4	-	-	-	-	-	pF
74AHCT	139									
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	8.0	V
$V_{OH}$	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = -50 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
		I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	4.0	-	40	-	80	μΑ
$\Delta I_{CC}$	additional supply current	per input pin; $V_{I} = V_{CC} - 2.1 \text{ V; other pins}$ at $V_{CC}$ or GND; $I_{O} = 0 \text{ A;}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	pF

### 10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		–40 °C to	+85 °C	–40 °C to	+125 °C	Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC1	39				•						
t <sub>pd</sub>		nAn to $n\overline{Y}n$ ; see Figure 5	[2]								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C <sub>L</sub> = 15 pF		-	5.5	11.0	1.0	13.0	1.0	14.0	ns
		C <sub>L</sub> = 50 pF		-	7.9	14.5	1.0	16.5	1.0	18.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C <sub>L</sub> = 15 pF		-	3.9	7.2	1.0	8.5	1.0	9.0	ns
		C <sub>L</sub> = 50 pF		-	5.6	9.2	1.0	10.5	1.0	11.5	ns
		nĒ to nŸn; see Figure 6	[2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C <sub>L</sub> = 15 pF		-	4.8	9.2	1.0	11.0	1.0	11.5	ns
		C <sub>L</sub> = 50 pF		-	6.9	12.7	1.0	14.5	1.0	16.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	3.4	6.3	1.0	7.5	1.0	8.0	ns
		C <sub>L</sub> = 50 pF		-	4.9	8.3	1.0	9.5	1.0	10.5	ns
$C_{PD}$	power dissipation capacitance	$f_i$ = 1 MHz; $V_I$ = GND to $V_{CC}$	[3]	-	26	-	-	-	-	-	pF
74AHCT	139; V <sub>CC</sub> = 4.	5 V to 5.5 V									
$t_{pd}$		nAn to $n\overline{Y}n$ ; see Figure 5	[2]								
	delay	C <sub>L</sub> = 15 pF		-	4.7	7.2	1.0	8.5	1.0	9.0	ns
		$C_L = 50 pF$		-	6.5	9.2	1.0	10.5	1.0	11.5	ns
		$n\overline{E}$ to $n\overline{Y}n$ ; see Figure 6	[2]								
		$C_L = 15 pF$		-	3.6	6.3	1.0	7.5	1.0	8.0	ns
		$C_L = 50 pF$		-	5.2	8.3	1.0	9.5	1.0	10.5	ns
C <sub>PD</sub>	power dissipation capacitance	$f_i$ = 1 MHz; $V_I$ = GND to $V_{CC}$	[3]	-	23	-	-	-	-	-	pF

<sup>[1]</sup> Typical values are measured at nominal supply voltage ( $V_{CC}$  = 3.3 V and  $V_{CC}$  = 5.0 V).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

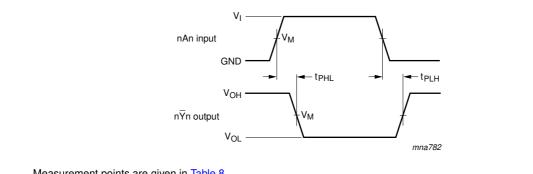
 $\Sigma(C_L\times V_{CC}{}^2\times f_o)$  = sum of the outputs.

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<sup>[2]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

<sup>[3]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

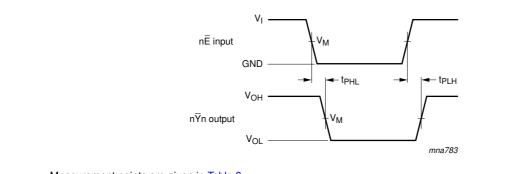
#### 11. Waveforms



Measurement points are given in Table 8.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

Fig 5. Address input to output propagation delays



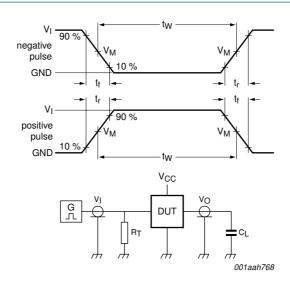
Measurement points are given in Table 8.

 $\ensuremath{V_{\text{OL}}}$  and  $\ensuremath{V_{\text{OH}}}$  are typical voltage output levels that occur with the output load.

Enable input to output propagation delays Fig 6.

Table 8. **Measurement points** 

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74AHC139	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT139	1.5 V	$0.5 \times V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $C_L$  = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

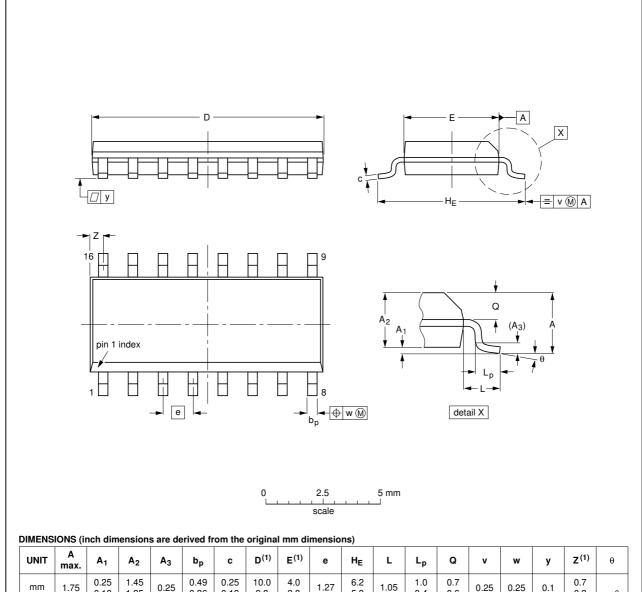
Table 9. Test data

Туре	Input		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74AHC139	V <sub>CC</sub>	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74AHCT139	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

### 12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

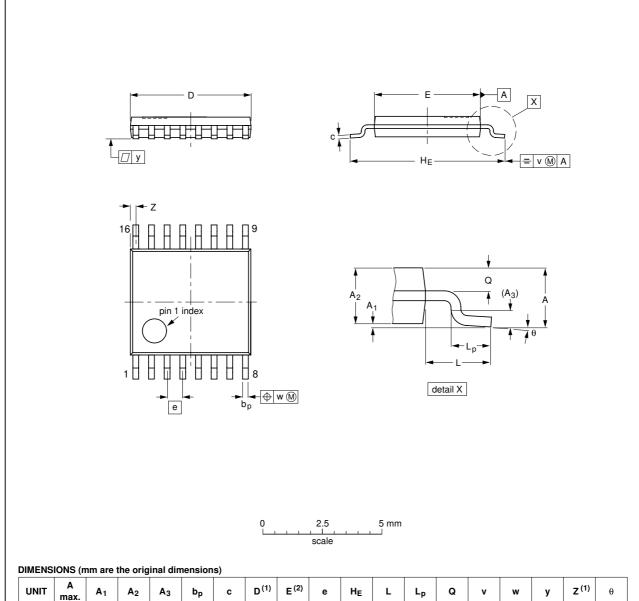
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	IEC JEDEC			PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				<del>99-12-27</del> 03-02-19	

Fig 8. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



						-,												
UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

		EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	MO-153				<del>99-12-27</del> 03-02-18
	IEC				IEC JEDEC JEHA

Fig 9. Package outline SOT403-1 (TSSOP16)

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### 13. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

### 14. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AHC_AHCT139_2	20080509	Product data sheet	-	74AHC_AHCT139_1		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
	-	have been adapted to the	• •			
	• <u>lable 6</u> : the	conditions for input leakage	ge current have been cha	inged.		
74AHC_AHCT139_1	19990901	Product specification	-	-		

#### 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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